

MSKSEMI

SEMICONDUCTOR



ESD



TVS



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MOV



GDT

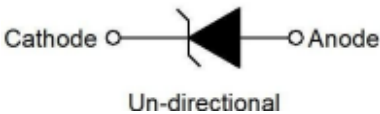


PLED

Product data sheet



SOD-123FL



Features

- Glass passivated or planar junction
- Excellent clamping capability
- Repetition rate (duty cycle): 0.01%
- Low profile package and low inductance
- Fast response time: typically less than 1.0ps from 0V to V_{BRmin} .
- High temperature soldering: 260°C/10s at terminals.
- For surface mounted applications in order to optimize board space.

Mechanical Characteristics

Package: SOD-123FL

- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Polarity: Color band denotes cathode except bi-directional models
- Weight: 0.017g
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- I/O Interface.
- Power lines
- Automotive and Telecommunication

Industrial Electronics

Electrical Characteristics (T=25°C)

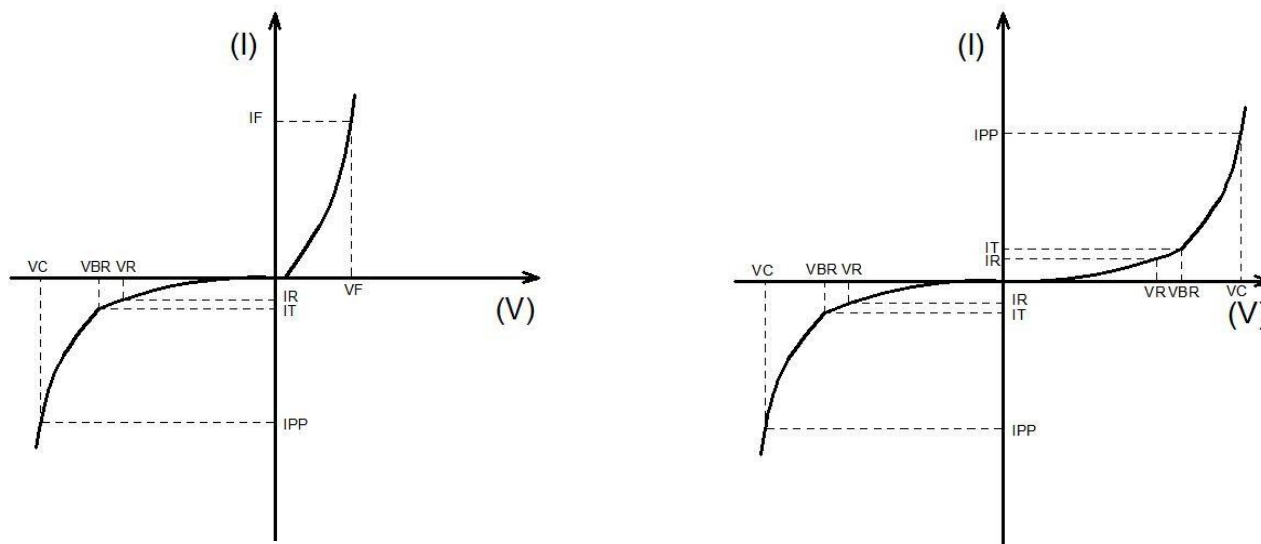
P/N	MARK	V_R	$I_R@V_R$	$V_{BR}@I_T$		I_T	$V_C@I_{PP}$	$I_{PP}^{\textcircled{1}}$
		V	μA	min(V)	max(V)	mA	max(V)	A
SMF3.3A	3.3A	3.3	200	5.2	6	10	8.0	25.00

Absolute Maximum Ratings($T=25^{\circ}\text{C}$, $\text{RH}=45\%-75\%$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak pulse power dissipation on 10/1000 μs waveform	P_{PP}	200	W
Steady state power dissipation at $T_L=75^{\circ}\text{C}$	$P_{M(AV)}$	1.0	W
Operating junction temperature range	T_j	-55 to +125	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Ratings And V-I Characteristics Curves ($T=25^{\circ}\text{C}$, unless otherwise noted)

FIG1: V-I cure characteristics



Symbol	Parameter
I_F	Mean Forward Current
V_F	Maximum Forward Voltage @ I_F
V_R	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_R
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}

Typical Characteristics

FIG2: Pulse Derating Curve

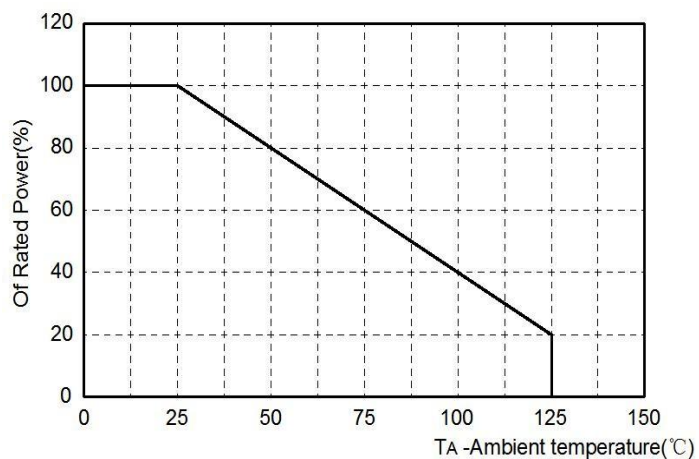


FIG3: Pulse Waveform

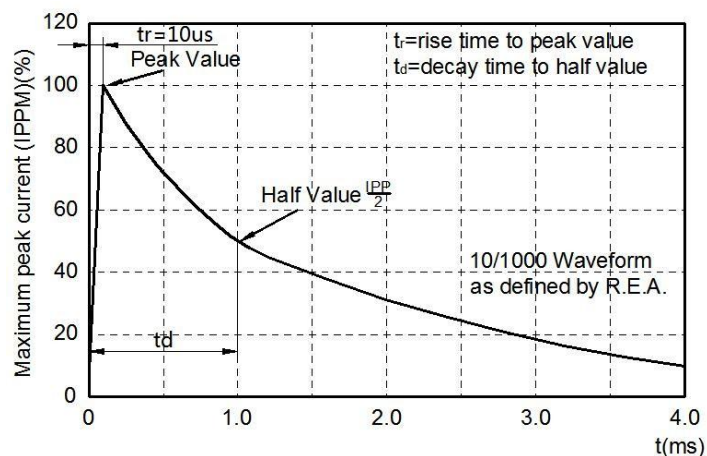


FIG4: Peak Pulse Power Rating Curve

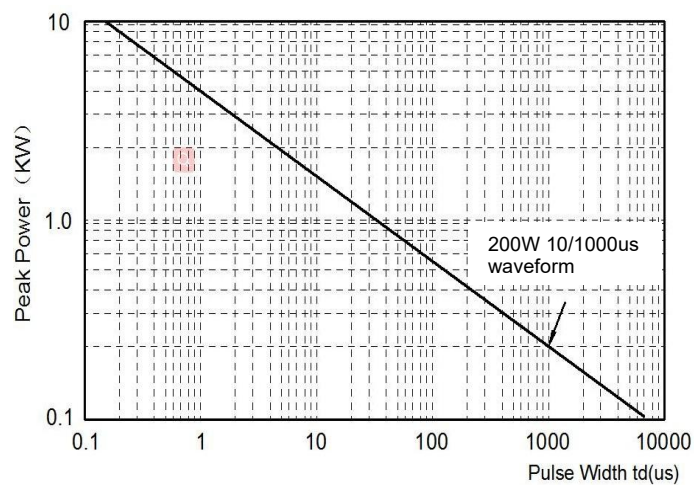
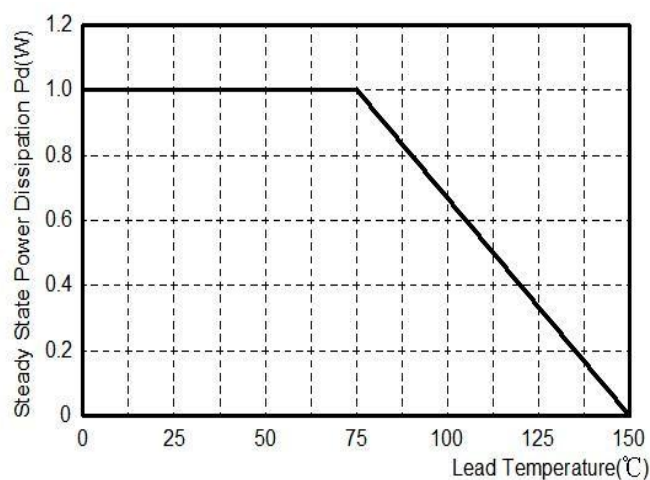
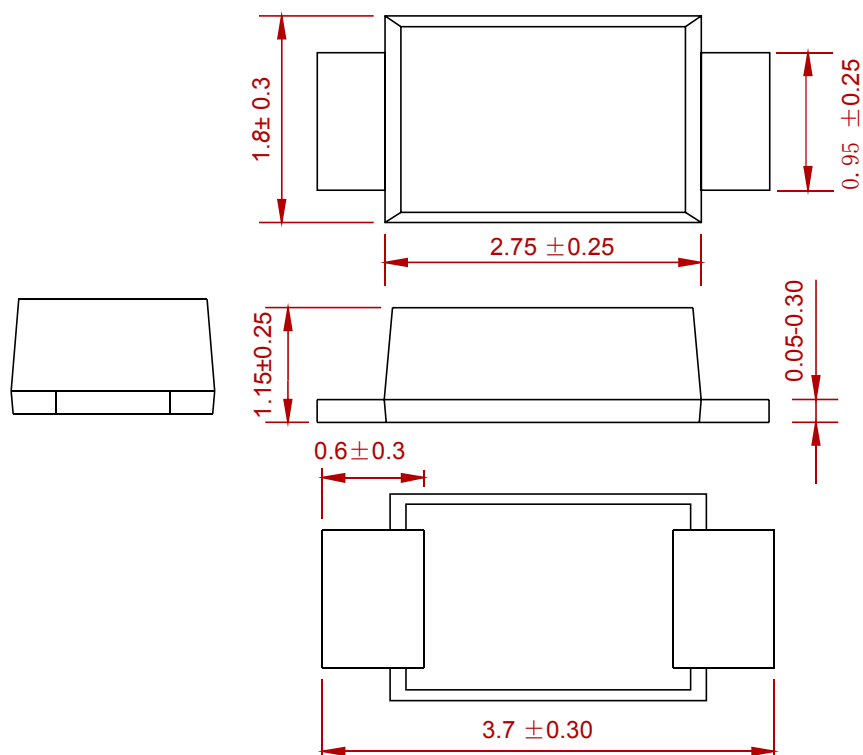


FIG5: Steady State Power Dissipation

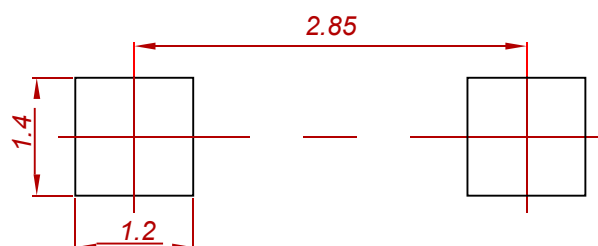


PACKAGE MECHANICAL DATA



Dimensions in millimeters

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SMF3.3A	SOD-123FL	3000

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